

# MA3Z551

## Silicon epitaxial planar type

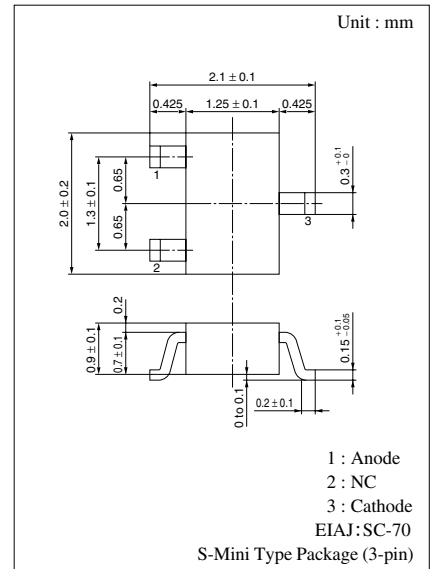
For high-frequency variable resistor attenuator

### ■ Features

- Small diode capacitance  $C_D$
- Large variable range of forward dynamic resistance  $r_f$
- Mini type package, allowing downsizing of equipment and automatic insertion through the taping package and magazine package

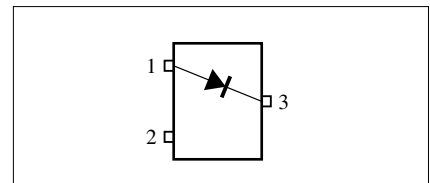
### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	$V_R$	40	V
Peak reverse voltage	$V_{RM}$	45	V
Forward current (DC)	$I_F$	100	mA
Power dissipation	$P_D$	150	mW
Operating ambient temperature	$T_{opr}$	-25 to +85	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$



Marking Symbol: MY

Internal Connection



### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	$I_R$	$V_R = 40\text{ V}$			100	nA
Forward voltage (DC)	$V_F$	$I_F = 100\text{ mA}$		1.05	1.2	V
Diode capacitance	$C_D$	$V_R = 15\text{ V}$ , $f = 1\text{ MHz}$		0.3	0.5	pF
Forward dynamic resistance*	$r_{f1}$	$I_F = 10\ \mu\text{A}$ , $f = 100\text{ MHz}$	1	2		k $\Omega$
	$r_{f2}$	$I_F = 10\text{ mA}$ , $f = 100\text{ MHz}$		6	10	$\Omega$

Note) 1. Rated input/output frequency: 100 MHz

2. \*:  $r_f$  measuring instrument: YHP MODEL 4191A RF IMPEDANCE ANALYZER

